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INFORMATION D	SECT OFFIDE	Application Number	NOT YET ASSIGNED 86445		
		Filing Date	July 17, 2006		
STATEMENT BY APPLICANT		First Named Inventor	KOZO NAKAMURA ET AL.		
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(use as many sheets as necessary)		Examiner Name	NOT YET ASSIGNED		
Sheet 1	of 1	Attorney Docket Number	1110/97825		

U.S. PATENT DOCUMENTS					
Examin er Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (f known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
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	1	JP 2003-257983	09-12-2003	Shin Etsu Handotai Co Ltd.		
	2	JP 2000-068280	03-03-2000	Sumitomo Metal Ind Ltd.		-
	3	JP 2003-318181	11-07-2003	Sumitomo Mitsubishi Silicon Corp		
	4	JP 11-147789	06-02-1999	Shin Etsu Handotai Co Ltd.		
	5	JP 02-263792	10-26-1990	Shin Etsu Handotai Co Ltd.		
	6	JP 04-130732	05-01-1992	Komatsu Electron Metals Co Ltd.		
	7	JP 04-298042	10-21-1992	Komatsu Electron Metals Co Ltd.	**************************************	
	8	JP 04-174300	06-23-1992	Toshiba Ceramics Co Ltd.		
	9	JP 05-102167	04-23-1993	Shin Etsu Handotai Co Ltd.	····	

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*			
	10	Hiroshi TAKENO et al, articled entitled "Practical Computer Simulation Technique To Predict Oxygen Precipitation Behavior In Czochralski Silicon Wafers For Various Thermal Processes," (Journal of Electrochemical Society, 1997, Vol. 144, No. 12, pp. 4340-4345 (the citation in ISR))	
	11	Koji SUEOKA et al., article entitled "Computer Simulation For Morphology, Size, and Density of Oxide Precipitates in CZ Silicon," (Journal of Electrochemical Society, 2003, Vol. 150, pp. G469-G475.)	
	12	M. Schrems, article entitled "Simulation of Oxygen Precipitation," (Semiconductors and Semimetals, 1994, Vol. 42, pp. 391-447) (Copyright © 1994 by Academic Press, Inc.)	***************************************

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